IN THE SPECIFICATION:

Delete the paragraph [0038] and replace it with the following new paragraph:

[0038] Figure 1 schematically depicts a lithographic projection apparatus 1 according to particular embodiments of the invention. The apparatus 1 may comprise a radiation system Ex, IL, for supplying a projection beam PB of radiation (e.g. EUV radiation), which in this particular case also comprises a radiation source LA; a first object table (mask table) MT provided with a mask holder for holding a mask MA (e.g. a reticle), and connected to a first positioning device for accurately positioning the mask with respect to item PL; a second object table (substrate table) WT provided with a substrate holder for holding a substrate W (e.g. a resist coated silicon wafer), and connected to a second positioning device for accurately positioning the substrate with respect to item PL; and a projection system ("lens") PL (e.g. mirror group) for imaging an irradiated portion of the mask MA onto a target portion C (e.g. comprising one or more dies) of the substrate W. The term table as used herein can also be considered or termed as a support. It should be understood that the term support or table broadly refers to a structure that supports, holds, or carries a substrate.

Delete the paragraph [0044] and replace it with the following new paragraph:

[0044] Figure 2 shows a downstream radical source 10 of an embodiment of the present invention. As understood by one of ordinary skill in the art, the downstream radical source 10 is disposed downstream of, or away from, the radiation source LA. This allows the radical source 10 to be operated at conditions necessary to effectively clean a target surface without affecting the beam of radiation PB that is generated by the radiation source LA. A flow of oxygen 2 or other gas, such as hydrogen or fluorine, is provided to flow through a tube [5] 4. The oxygen flows through a plasma region 3 which may be generated, for example, by an RF coil or a microwave or RF cavity. Other means of generating the plasma region will also be suitable. Alternatively, the radicals may be created in a continuous or burst mode DC discharge. In the plasma region 3, neutral and ionized active particles are generated. The ionized particles may be neutralized by collisions with the tube walls 5 or with a Faraday grid 6 that may be located at, for example, the tube orifice. The neutral radicals, which will react with a contaminant, such as carbon, but will not damage the surface, survive these collisions and exit the tube as beam 7. The neutral radicals react with, for example, a carbon

contaminant on the optical surface 8 to form CO and CO_2 9 which desorb from the surface and disperse into the lithographic apparatus. In the case of apparatus employing EUV radiation, the CO and CO_2 gases are subsequently extracted by a vacuum system.